

[illegible]

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28. A plasma processing apparatus as defined in Claim 18, wherein the dielectric tube is protruded by 1 to 10mm from a surface of the metal body or the facing electrode.

29. (Amended) A plasma processing apparatus as defined in Claim 27 ~~or 28~~, wherein the dielectric tube is disposed such that it covers an edge of a hole of the metal body or the facing electrode.

30. A plasma processing apparatus as defined in Claim 18, wherein the hole of the dielectric tube is 0.2 to 2mm in diameter.

31. A plasma processing apparatus as defined in Claim 18, wherein the hole of the dielectric tube is 0.4 to 0.8mm in diameter.

32. A plasma processing apparatus as defined in Claim 18, wherein a frequency of high-frequency power applied to the plasma source, the substrate electrode or the facing electrode is 50MHz to 3GHz.

33. A plasma processing apparatus as defined in Claim 24, wherein the dielectric tube is a bolt screwed in a tap given to the metal body or the facing electrode.

34. A plasma processing apparatus as defined in Claim 24, wherein the dielectric tube has a spot facing for screwdriver or wrench on a side of an inner wall of the vacuum chamber for rotating and screwing the dielectric tube in the metal plate or the facing electrode.

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35. A plasma processing apparatus as defined in Claim 24, wherein the dielectric tube is protruded by 0.5 to 20mm from a surface of the metal body or the facing electrode.

36. A plasma processing apparatus as defined in Claim 24, wherein the dielectric tube is protruded by 1 to 10mm from a surface of the metal body or the facing electrode.

37. (Amended) A plasma processing apparatus as defined in Claim ²⁸
~~27 or 28~~, wherein the dielectric tube is disposed such that it covers an edge of a hole of the metal body or the facing electrode.

38. A plasma processing apparatus as defined in Claim 24, wherein the hole of the dielectric tube is 0.2 to 2mm in diameter.

39. A plasma processing apparatus as defined in Claim 24, wherein the hole of the dielectric tube is 0.4 to 0.8mm in diameter.

40. A plasma processing apparatus as defined in Claim 24, wherein a frequency of high-frequency power applied to the plasma source, the substrate electrode or the facing electrode is 50MHz to 3GHz.